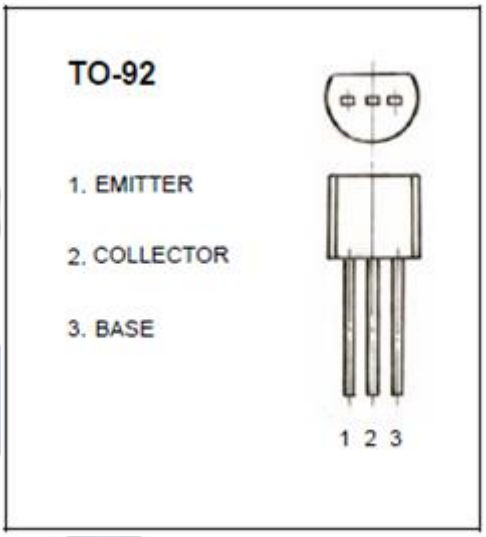
isc Silicon PNP Transistor 2SA1015



DESCRIPTION

- High Voltage and High Current
  Vceo=-50V(Min.)，Ic=-150mA(Max)
- Excellent hFE Linearity
- Low Noise
- Complement to Type 2SC1815

APPLICATIONS

- Audio frequency general purpose amplifier Applications
- Driver stage amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Curren	-150	mA
I_B	Base Curren	-50	mA
P_C	Collector Power Dissipation @T_C=25℃	400	mW
T_J	Junction Temperature	125	℃
T_{stg}	Storage Temperature Range	-55~125	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -100mA ; I_B= -10mA			-0.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -100mA ; I_B= -10mA			-1.1	V
I_{CBO}	Emitter Cutoff Current	V_{CB}= -50V; I_E= 0			-0.1	μA
I_{EBO}	Collector Cutoff Current	V_{EB}= -5V; I_C= 0			-0.1	μA
$h_{FE(1)}$	DC Current Gain	I_C= -2mA ; V_{CE}= -6V	70		400	
$h_{FE(2)}$	DC Current Gain	I_C= -150mA ; V_{CE}= -6V	25			
f_T	Current-Gain—Bandwidth Product	I_C= -1mA; V_{CE}= -10V;	80			MHz
Cob	Collector Output Capacitance	V_{CB}=-10V; I_E=0; f=1MHz			7	pF
NF	Noise Figure	V_{CE}=-6V,I_C=-0.1mA;f=1KHz, R_G=10KΩ			10	dB

◆ **$h_{FE(1)}$ Classifications**

O	Y	GR
70-140	120-240	200-400